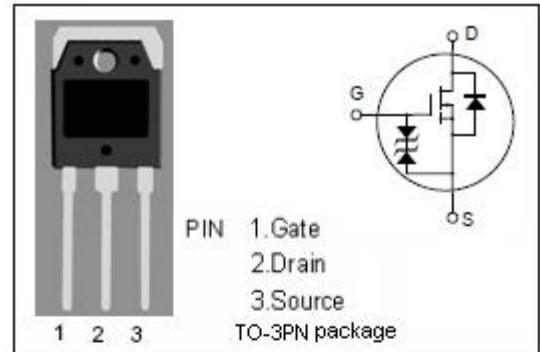


## isc N-Channel MOSFET Transistor

2SK2081-01

## DESCRIPTION

- Drain Current  $I_D = 12A @ T_c=25^\circ C$
- Drain Source Voltage-  
:  $V_{DSS} = 500V$ (Min)
- Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



## APPLICATIONS

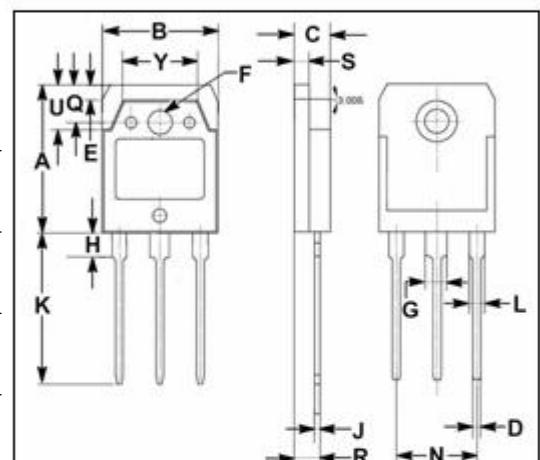
- Switching regulators
- UPS
- DC-DC Converters
- General purpose power amplifier

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{DSS}$	Drain-Source Voltage ( $V_{GS}=0$ )	500	V
$V_{GS}$	Gate-Source Voltage	$\pm 30$	V
$I_D$	Drain Current-continuous@ $T_c=25^\circ C$	12	A
$I_{D(puls)}$	Pulsed Drain Current	48	A
$P_{tot}$	Total Dissipation@ $T_c=25^\circ C$	125	W
$T_j$	Max. Operating Junction Temperature	150	°C
$T_{stg}$	Storage Temperature Range	-55~150	°C

## • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th j-c}$	Thermal Resistance, Junction to Case	1.00	°C/W
$R_{th j-a}$	Thermal Resistance, Junction to Ambient	35	°C/W



DIM	mm	
	MIN	MAX
A	19.60	20.10
B	15.50	15.70
C	4.70	4.90
D	0.90	1.10
E	1.90	2.10
F	3.40	3.60
G	2.90	3.20
H	3.20	3.40
J	0.595	0.605
K	20.00	20.70
L	1.90	2.20
N	10.89	10.91
Q	4.90	5.10
R	3.35	3.45
S	1.995	2.100
U	5.90	6.10
Y	9.90	10.10

## isc N-Channel Mosfet Transistor

2SK2081-01

• ELECTRICAL CHARACTERISTICS ( $T_c=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	MIN	TYPE	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0$ ; $I_D=1\text{mA}$	500			V
$V_{GS(\text{th})}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$ ; $I_D=1\text{mA}$	2.5	3.0	3.5	V
$V_{SD}$	Diode Forward on-Voltage	$I_F=2I_{DR}$ ; $V_{GS}=0$		1.3	1.95	V
$R_{DS(\text{on})}$	Drain-Source On-Resistance	$V_{GS}=10\text{V}$ ; $I_D=6\text{A}$		0.45	0.6	$\Omega$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS}=\pm 30\text{V}$ ; $V_{DS}=0$			$\pm 100$	nA
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS}=500\text{V}$ ; $V_{GS}=0$			500	$\mu\text{A}$
$C_{iss}$	Input Capacitance	$V_{DS}=25\text{V}$ ; $V_{GS}=0\text{V}$ ; $f_T=1\text{MHz}$		2200	3300	pF
$C_{rss}$	Reverse Transfer Capacitance			55	85	
$C_{oss}$	Output Capacitance			230	345	
$t_r$	Rise Time	$V_{GS}=10\text{V}$ ; $I_D=12\text{A}$ ; $V_{DD}=300\text{V}$ ; $R_L=10\Omega$		55	85	ns
$t_{d(on)}$	Turn-on Delay Time			25	40	
$t_f$	Fall Time			60	90	
$t_{d(off)}$	Turn-off Delay Time			110	165	

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